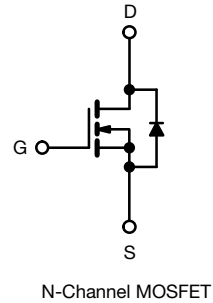
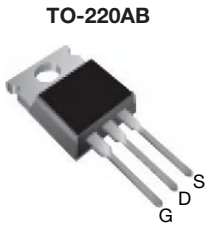


## SGSP363-VB Datasheet Power MOSFET

PRODUCT SUMMARY		
$V_{DS}$ (V)	250	
$R_{DS(on)}$ ( $\Omega$ )	$V_{GS} = 10\text{ V}$	0.19
$Q_g$ max. (nC)	68	
$Q_{gs}$ (nC)	11	
$Q_{gd}$ (nC)	35	
Configuration	Single	

### FEATURES

- Dynamic  $dV/dt$  rating
- Repetitive avalanche rated
- Fast switching
- Ease of paralleling
- Simple drive requirements



ABSOLUTE MAXIMUM RATINGS ( $T_C = 25\text{ }^\circ\text{C}$ , unless otherwise noted)				
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		$V_{DS}$	250	V
Gate-Source Voltage		$V_{GS}$	$\pm 20$	
Continuous Drain Current	$V_{GS}$ at 10 V	$I_D$	$T_C = 25\text{ }^\circ\text{C}$	14
			$T_C = 100\text{ }^\circ\text{C}$	8.5
Pulsed Drain Current <sup>a</sup>		$I_{DM}$	56	A
Linear Derating Factor			1.0	$W/^\circ\text{C}$
Single Pulse Avalanche Energy <sup>b</sup>		$E_{AS}$	550	mJ
Repetitive Avalanche Current <sup>a</sup>		$I_{AR}$	14	A
Repetitive Avalanche Energy <sup>a</sup>		$E_{AR}$	13	mJ
Maximum Power Dissipation		$P_D$	125	W
$T_C = 25\text{ }^\circ\text{C}$				
Peak Diode Recovery $dV/dt$ <sup>c</sup>		$dV/dt$	4.8	V/ns
Operating Junction and Storage Temperature Range		$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$
Soldering Recommendations (Peak temperature) <sup>d</sup>		for 10 s	300	
Mounting Torque	6-32 or M3 screw		10	lbf · in
			1.1	N · m

### Notes

- Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- $V_{DD} = 50\text{ V}$ , starting  $T_J = 25\text{ }^\circ\text{C}$ ,  $L = 4.5\text{ mH}$ ,  $R_g = 25\text{ }\Omega$ ,  $I_{AS} = 14\text{ A}$  (see fig. 12).
- $I_{SD} \leq 14\text{ A}$ ,  $dI/dt \leq 150\text{ A}/\mu\text{s}$ ,  $V_{DD} \leq V_{DS}$ ,  $T_J \leq 150\text{ }^\circ\text{C}$ .
- 1.6 mm from case.

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	$R_{thJA}$	-	62	°C/W
Case-to-Sink, Flat, Greased Surface	$R_{thCS}$	0.50	-	
Maximum Junction-to-Case (Drain)	$R_{thJC}$	-	1.0	

SPECIFICATIONS ( $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	250	-	-	V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 1\text{ mA}$	-	0.34	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{GS} = \pm 20\text{ V}$	-	-	$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$	-	-	25	$\mu\text{A}$
		$V_{DS} = 200\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	250	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 8.4\text{ A}^b$	-	0.19	-	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 50\text{ V}, I_D = 8.4\text{ A}^b$	6.7	-	-	S
<b>Dynamic</b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1.0\text{ MHz}, \text{ see fig. 5}$	-	1300	-	pF
Output Capacitance	$C_{oss}$		-	330	-	
Reverse Transfer Capacitance	$C_{rss}$		-	85	-	
Total Gate Charge	$Q_g$	$V_{GS} = 10\text{ V}, I_D = 7.9\text{ A}, V_{DS} = 200\text{ V}, \text{ see fig. 6 and 13}^b$	-	-	68	nC
Gate-Source Charge	$Q_{gs}$		-	-	11	
Gate-Drain Charge	$Q_{gd}$		-	-	35	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 125\text{ V}, I_D = 7.9\text{ A}, R_g = 9.1\text{ }\Omega, R_D = 8.7\text{ }\Omega, \text{ see fig. 10}^b$	-	11	-	ns
Rise Time	$t_r$		-	24	-	
Turn-Off Delay Time	$t_{d(off)}$		-	53	-	
Fall Time	$t_f$		-	49	-	
Internal Drain Inductance	$L_D$	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	$L_S$		-	7.5	-	
Gate Input Resistance	$R_g$	$f = 1\text{ MHz}, \text{ open drain}$	0.3	-	1.2	$\Omega$
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	14	A
Pulsed Diode Forward Current <sup>a</sup>	$I_{SM}$		-	-	56	
Body Diode Voltage	$V_{SD}$	$T_J = 25\text{ }^\circ\text{C}, I_S = 14\text{ A}, V_{GS} = 0\text{ V}^b$	-	-	1.8	V
Body Diode Reverse Recovery Time	$t_{rr}$	$T_J = 25\text{ }^\circ\text{C}, I_F = 7.9\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}^b$	-	250	500	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	2.3	4.6	$\mu\text{C}$
Forward Turn-On Time	$t_{on}$	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S$ and $L_D$ )				

**Notes**

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
- b. Pulse width  $\leq 300\text{ }\mu\text{s}$ ; duty cycle  $\leq 2\%$ .

**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C**



**Fig. 4 - Normalized On-Resistance vs. Temperature**



**Fig. 2 - Typical Output Characteristics, T<sub>C</sub> = 150 °C**



**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**



**Fig. 3 - Typical Transfer Characteristics**



**Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage**



Fig. 7 - Typical Source-Drain Diode Forward Voltage



Fig. 9 - Maximum Drain Current vs. Case Temperature

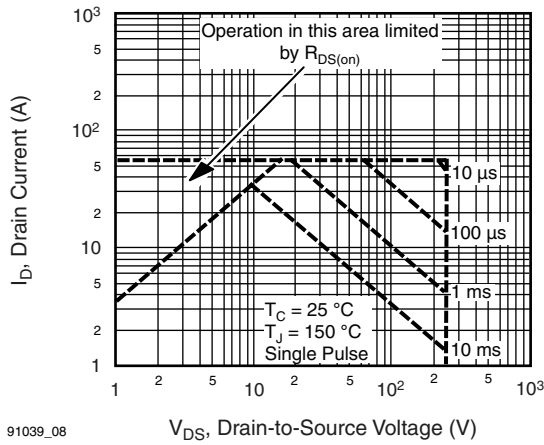


Fig. 8 - Maximum Safe Operating Area

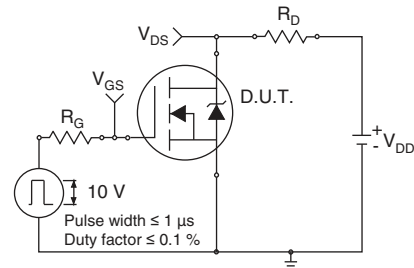


Fig. 10a - Switching Time Test Circuit

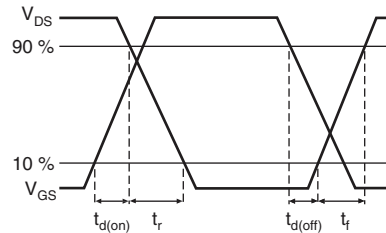


Fig. 10b - Switching Time Waveforms



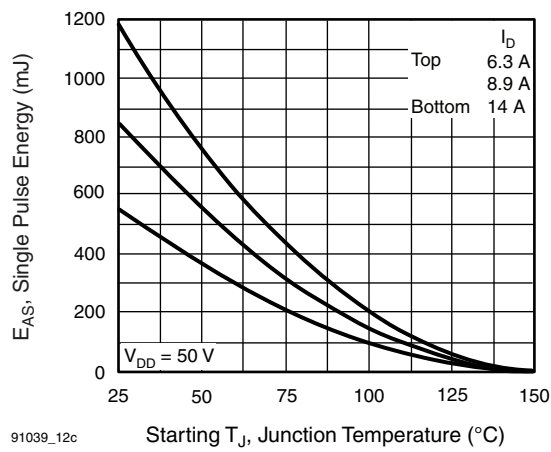
Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



Fig. 12a - Unclamped Inductive Test Circuit



Fig. 12b - Unclamped Inductive Waveforms



91039\_12c

Fig. 12c - Maximum Avalanche Energy vs. Drain Current



Fig. 13a - Basic Gate Charge Waveform



Fig. 13b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note  
a.  $V_{GS} = 5 V$  for logic level devices

Fig. 14 - For N-Channel

TO-220-1



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.24	4.65	0.167	0.183
b	0.69	1.02	0.027	0.040
b(1)	1.14	1.78	0.045	0.070
c	0.36	0.61	0.014	0.024
D	14.33	15.85	0.564	0.624
E	9.96	10.52	0.392	0.414
e	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.10	6.71	0.240	0.264
J(1)	2.41	2.92	0.095	0.115
L	13.36	14.40	0.526	0.567
L(1)	3.33	4.04	0.131	0.159
Ø P	3.53	3.94	0.139	0.155
Q	2.54	3.00	0.100	0.118

ECN: X15-0364-Rev. C, 14-Dec-15  
DWG: 6031

**Note**

- M\* = 0.052 inches to 0.064 inches (dimension including protrusion), heatsink hole for HVM

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